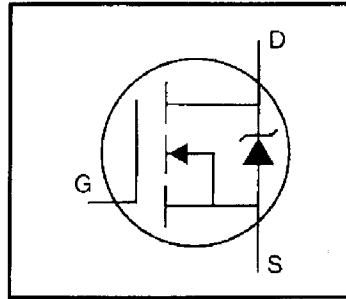


# IRFZ46

## HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements

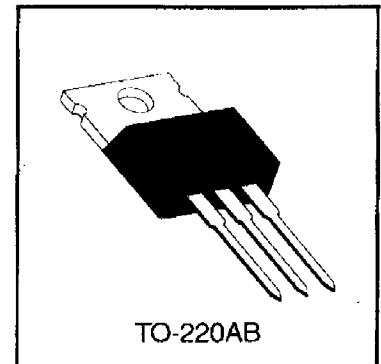


$$V_{DSS} = 50V$$

$$R_{DS(on)} = 0.024\Omega$$

$$I_D = 50^*A$$

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



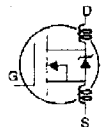
### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	50*	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	38	
$I_{DM}$	Pulsed Drain Current ①	220	
$P_D @ T_C = 25^\circ C$	Power Dissipation	150	W
	Linear Derating Factor	1.0	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	100	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf·in (1.1 N·m)	

### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	50	—	—	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.057	—	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.024	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =32A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
g <sub>fs</sub>	Forward Transconductance	27	—	—	S	V <sub>DS</sub> =25V, I <sub>D</sub> =32A ④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V
		—	—	250		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> =20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> =-20V
Q <sub>g</sub>	Total Gate Charge	—	—	66	nC	I <sub>D</sub> =54A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	21		V <sub>DS</sub> =48V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	25		V <sub>GS</sub> =10V See Fig. 6 and 13 ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	12	—	ns	V <sub>DD</sub> =28V
t <sub>r</sub>	Rise Time	—	120	—		I <sub>D</sub> =54A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	42	—		R <sub>G</sub> =9.1Ω
t <sub>f</sub>	Fall Time	—	95	—		R <sub>D</sub> =0.49Ω See Figure 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	1800	—	pF	V <sub>GS</sub> =0V
C <sub>oss</sub>	Output Capacitance	—	960	—		V <sub>DS</sub> =25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	160	—		f=1.0MHz See Figure 5

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	50*	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	220		
V <sub>SD</sub>	Diode Forward Voltage	—	—	2.5	V	T <sub>J</sub> =25°C, I <sub>S</sub> =54A, V <sub>GS</sub> =0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	66	99	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =54A
Q <sub>rr</sub>	Reverse Recovery Charge	—	0.17	0.31	μC	di/dt=100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

③ I<sub>SD</sub>≤54A, di/dt≤250A/μs, V<sub>DD</sub>≤V<sub>(BR)DSS</sub>, T<sub>J</sub>≤175°C

② V<sub>DD</sub>=25V, starting T<sub>J</sub>=25°C, L=34μH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=54A (See Figure 12)

④ Pulse width ≤ 300 μs; duty cycle ≤2%.

\* Current limited by the package, (Die Current =54A)